



ABSTRACT

A method for texturing surfaces of silicon wafers comprising the steps of dipping the silicon wafers in an etching solution of water, concentrated hydrofluoric acid and concentrated nitric acid and setting a temperature for the etching solution. The etching solution comprises, in percent, 20% to 55% water, 10% to 40% concentrated hydrofluoric acid and 20% to 60% concentrated nitric acid and the temperature of the etching solution is between 0 and 15 degrees Celsius.